AMENDMENT TO THE CLAIMS

1. (currently amended) An electrically programmable memory ~~element~~, comprising:

a programmable resistance material;

a threshold switching material comprising a chalcogen element; and

a first layer of a dielectric material between said programmable resistance material and said threshold switching material, said dielectric material including silicon nitride.

2. (currently amended) The memory ~~element~~ of claim 1, further comprising a second layer of a dielectric material, said threshold switching material being between said first layer ~~of said dielectric material~~ and said second layer ~~of said dielectric material~~.

3. (currently amended) The memory ~~element~~ of claim 2, further comprising a third layer of a dielectric material, said programmable resistance material being between said third layer ~~of said dielectric material~~ and said first layer ~~of said dielectric material~~.

4. (currently amended) The memory ~~element~~ of claim 1, further comprising a second layer of a dielectric material, said programmable resistance material being between said first layer ~~of said dielectric material~~ and said second layer ~~of said dielectric material~~.

5. (currently amended) The memory ~~element~~ of claim 1, wherein said programmable resistance material is a phase-change material.

6. (currently amended) The memory ~~element~~ of claim 1, wherein said programmable resistance material comprises a chalcogen element.

Claim 7 (canceled)

8. (currently amended) The memory ~~element~~ of claim 1, wherein said first layer ~~of said dielectric material~~ has a thickness of less than 100 Angstroms.

Claims 9-20 (cancelled).